

NOR GATE

4000B-DUAL 3 INPUT PLUS INVERTER

4001B-QUAD 2 INPUT

4002B-DUAL 4 INPUT

4025B TRIPLE 3 INPUT

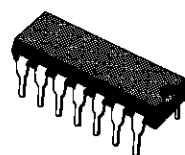
- PROPAGATION DELAY TIME = 60 ns (typ.) AT $C_L = 50$ pF, $V_{DD} = 10$ V
- BUFFERED INPUTS AND OUTPUTS
- STANDARDIZED SYMMETRICAL OUTPUT CHARACTERISTICS
- QUIESCENT CURRENT SPECIFIED TO 20 V FOR HCC DEVICE
- 5V, 10V AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100nA AT 18V AND 25 °C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N. 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF B SERIES CMOS DEVICES"

DESCRIPTION

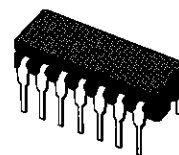
The **HCC4000B**, **HCC4001B**, **HCC4002B** and **HCC4025B** (extended temperature range) and **HCF4000B**, **HCF4001B**, **HCF4002B** and **HCF4025B** (intermediate temperature range) are monolithic integrated circuit, available in 14-lead dual in line plastic or ceramic package and plastic

micropackage.

The **HCC/HCF4000B**, **HCC/HCF4001B**, **HCC/HCF4002B** and **HCC/HCF4025B** nor gate provide the system designer with direct implementation of the nor function and supplement the existing family of COS/MOS gates. All inputs and outputs are buffered.



EY
(Plastic Package)



F
(Ceramic Package)



M1
(Micro Package)



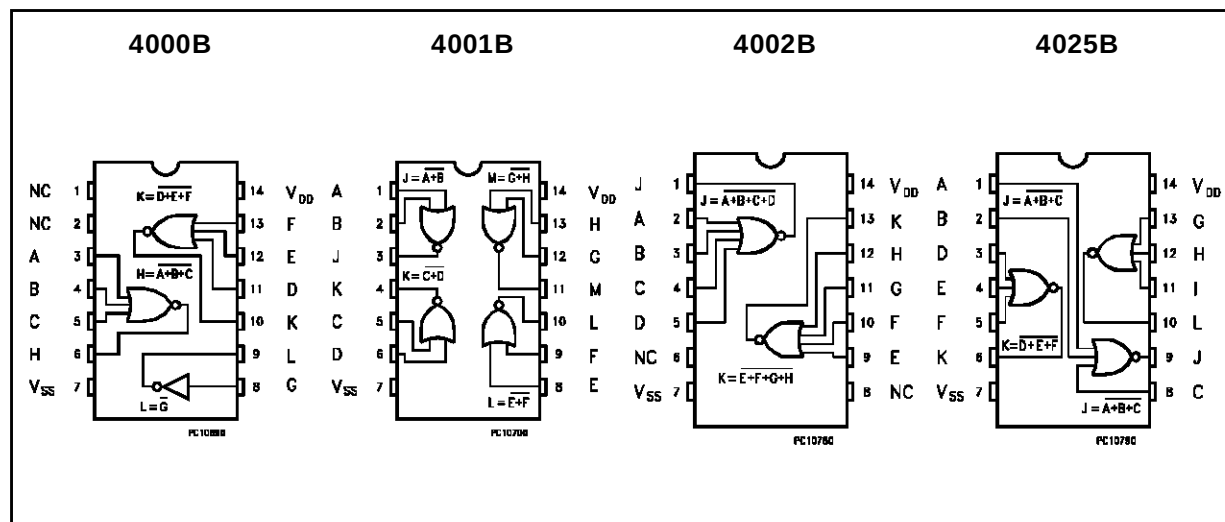
C1
(Chip Carrier)

ORDER CODES :

HCCXXXXBF
HCFXXXXBEY

HCFXXXXBM1
HCFXXXXBC1

PIN CONNECTIONS



ABSOLUTE MAXIMUM RATING

Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage: HCC Types HCF Types	-0.5 to +20 -0.5 to +18	V V
V _I	Input Voltage	-0.5 to V _{DD} + 0.5	V
I _I	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for T _{op} = Full Package Temperature Range	200 100	mW mW
T _{op}	Operating Temperature: HCC Types HCF Types	-55 to +125 -40 to +85	°C °C
T _{stg}	Storage Temperature	-65 to +150	°C

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

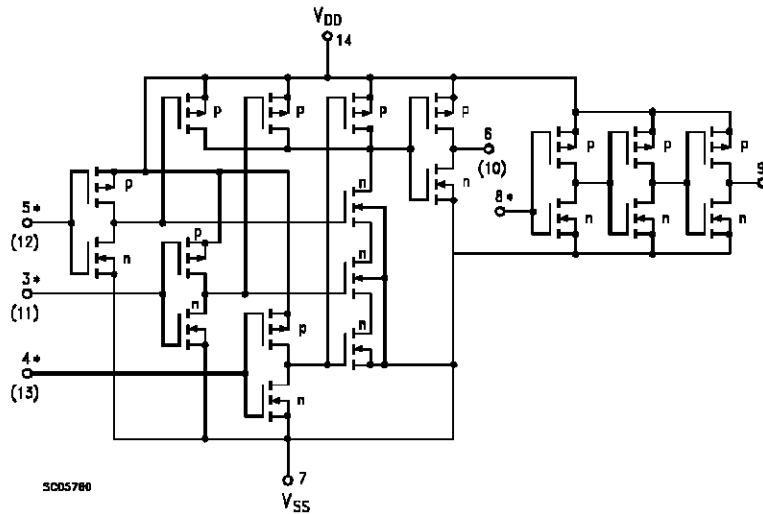
* All voltage values are referred to V_{SS} pin voltage.

RECOMMENDED OPERATING CONDITIONS

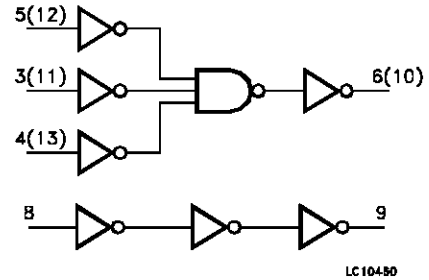
Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage: HCC Types HCF Types	3 to 18 3 to 15	V V
V _I	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature: HCC Types HCF Types	-55 to +125 -40 to +85	°C °C

SCHEMATIC AND LOGIC DIAGRAMS

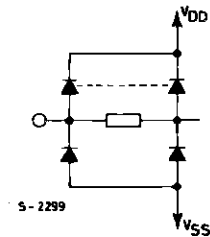
4000B



INVERTER AND 1 OF 2 GATES (NUMBERS IN PARANTHESES ARE THERMINAL FOR SECOND GATE)

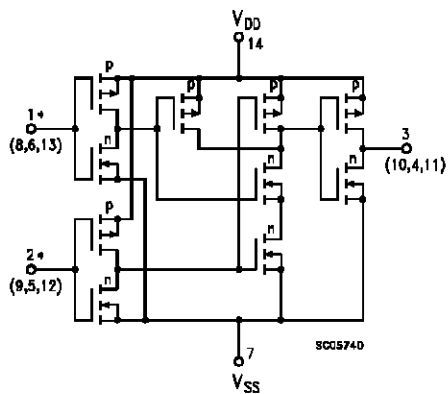


LC10430

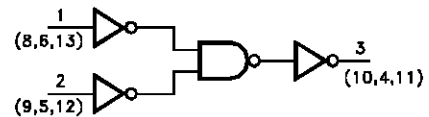


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COS/MOS PROTECTION NETWORK

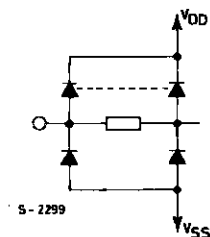
4001B



1 OF 4 GATES (NUMBERS IN PARANTHESES ARE THERMINAL FOR OTHER GATE)



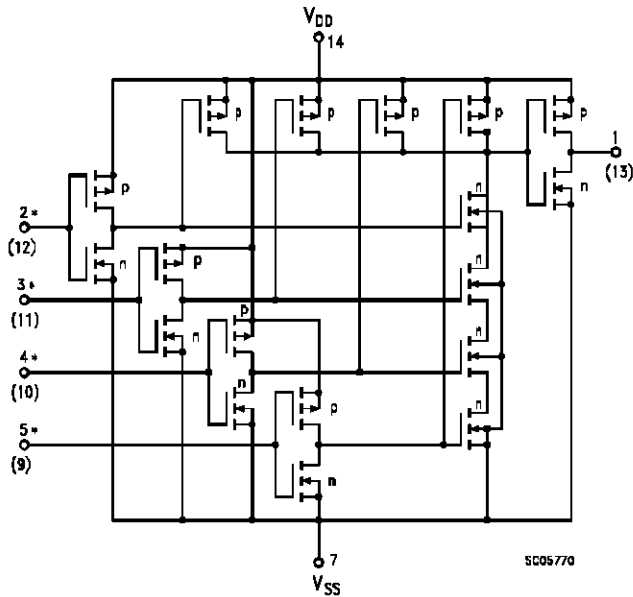
LC10430



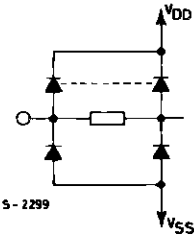
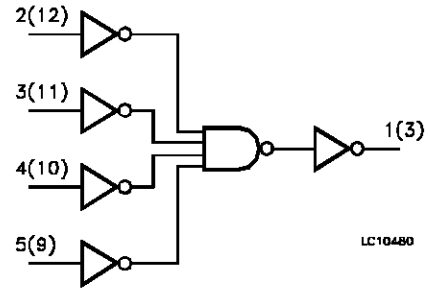
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SCHEMATIC AND LOGIC DIAGRAMS (continued)

4002B

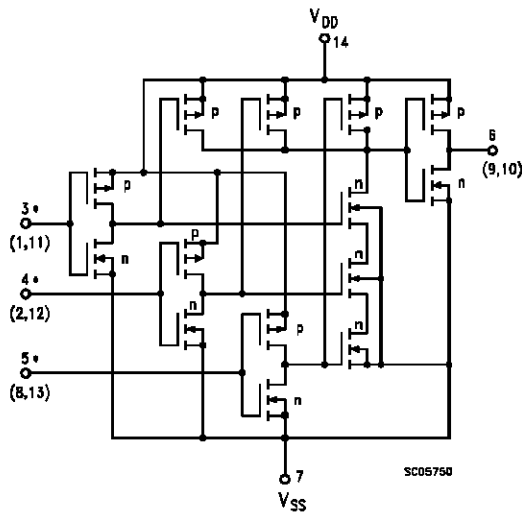


1 OF 2 GATES (NUMBERS IN PARANtheses ARE THERMINAL FOR SEC-
OND GATE)

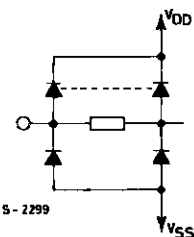
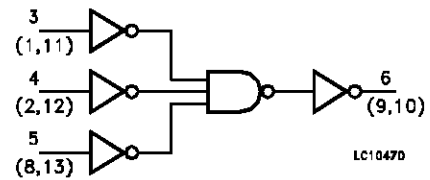


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COS/MOS PROTECTION NETWORK

4025B



INVERTER AND 1 OF 3 GATES (NUMBERS IN PARANtheses ARE
THERMINAL FOR OTHER GATES)



ALL INPUTS ARE PROTECTED BY
COS/MOS PROTECTION NETWORK

STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

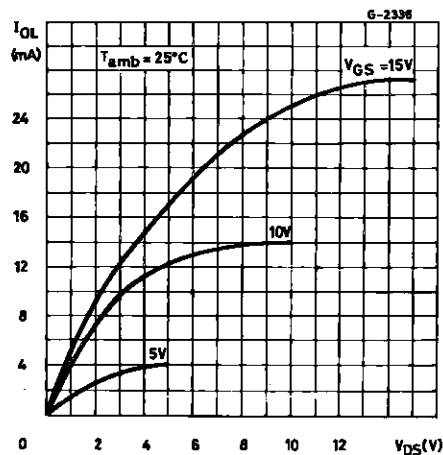
Symbol	Parameter		Test Conditions				Value							Unit
			V _I (V)	V _O (V)	I _O (μA)	V _{DD} (V)	T _{LOW} *		25 °C			T _{HIGH} *		
							Min.	Max.	Min.	Typ.	Max.	Min.	Max.	
I _L	Quiescent Current	HCC Types	0/5			5		0.25		0.01	0.25		7.5	μA
			0/10			10		0.5		0.01	0.5		15	
			0/15			15		1		0.01	1		30	
			0/20			20		5		0.02	5		150	
		HCF Types	0/5			5		1		0.01	1		7.5	
			0/10			10		2		0.01	2		15	
			0/15			15		4		0.01	4		30	
V _{OH}	Output High Voltage	0/5		< 1	5	4.95		4.95			4.95		V	
		0/10		< 1	10	9.95		9.95			9.95			
		0/15		< 1	15	14.95		14.95			14.95			
V _{OL}	Output Low Voltage	5/0		< 1	5		0.05			0.05		0.05	V	
		10/0		< 1	10		0.05			0.05		0.05		
		15/0		< 1	15		0.05			0.05		0.05		
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5			3.5		V	
			1/9	< 1	10	7		7			7			
			1.5/13.5	< 1	15	11		11			11			
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1.5			1.5		1.5	V	
			9/1	< 1	10		3			3		3		
			13.5/1.5	< 1	15		4			4		4		
I _{OH}	Output Drive Current	HCC Types	0/5	2.5		5	-2		-1.6	-3.2		-1.15		mA
			0/5	4.6		5	-0.64		-0.51	-1		-0.36		
			0/10	9.5		10	-1.6		-1.3	-2.6		-0.9		
			0/15	13.5		15	-4.2		-3.4	-6.8		-2.4		
		HCF Types	0/5	2.5		5	-1.53		-1.36	-3.2		-1.1		
			0/5	4.6		5	-0.52		-0.44	-1		-0.36		
			0/10	9.5		10	-1.3		-1.1	-2.6		-0.9		
			0/15	13.5		15	-3.6		-3.0	-6.8		-2.4		
I _{OL}	Output Sink Current	HCC Types	0/5	0.4		5	0.64		0.51	1		0.36		mA
			0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8		2.4		
		HCF Types	0/5	0.4		5	0.52		0.44	1		0.36		
			0/10	0.5		10	1.3		1.1	2.6		0.9		
			0/15	1.5		15	3.6		3.0	6.8		2.4		
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input	18		±0.1		±10 ⁻⁵	±0.1		±1	μA	
		HCF Types	0/15		15		±0.3		±10 ⁻⁵	±0.3		±1		
C _I	Input Capacitance			Any Input					5	7.5			pF	

* T_{LOW} = -55 °C for HCC device; -40 °C for HCF device.* T_{HIGH} = +125 °C for HCC device; +85 °C for HCF device.The Noise Margin for both "1" and "0" level is: 1V min. with V_{DD} = 5 V, 2 V min. with V_{DD} = 10 V, 2.5 V min. with V_{DD} = 15 V

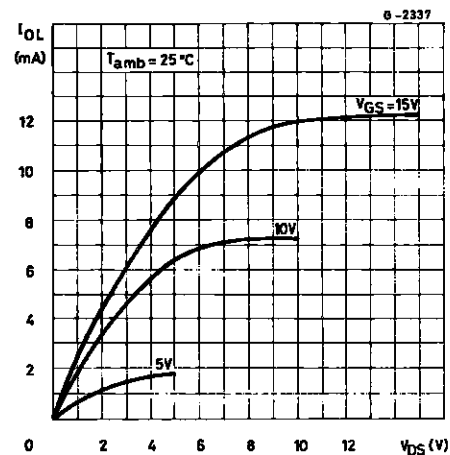
DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$, $C_L = 50\text{ pF}$, $R_L = 200\text{ K}\Omega$, typical temperature coefficient for all V_{DD} values is $03\text{ }^{\circ}\text{C}/^{\circ}\text{C}$, all input rise and fall times = 20 ns)

Symbol	Parameter	Test Conditions		Value			Unit
			V_{DD} (V)	Min.	Typ.	Max.	
t_{PHL} t_{PLH}	Propagation Delay Time		5		125	250	ns
			10		60	120	
			5		45	90	
t_{THL} t_{TLH}	Transition Time		5		100	200	ns
			10		50	100	
			15		40	80	

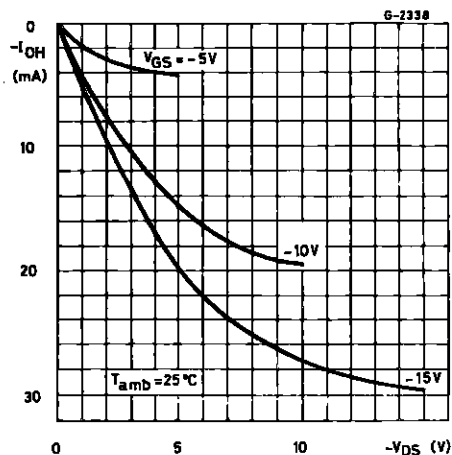
Typical Output Low (sink) Current Characteristics



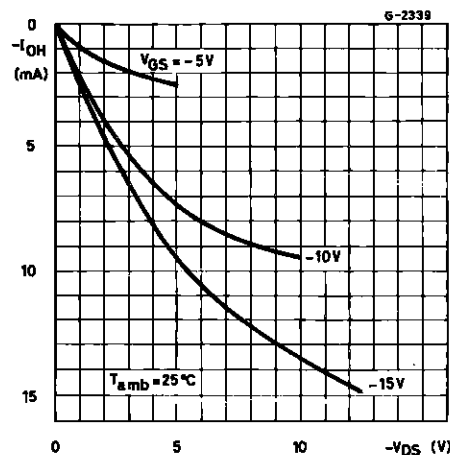
Minimum Output Low (sink) Current Characteristics



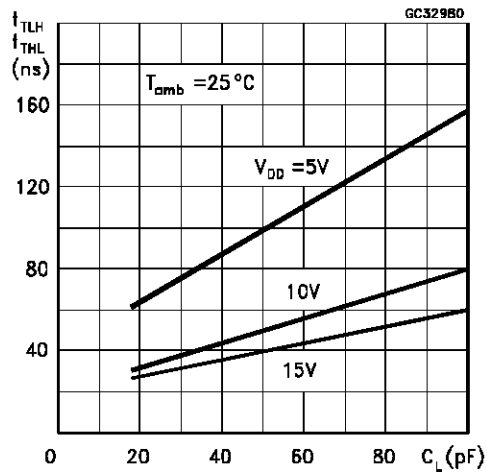
Typical Output High (source) Current Characteristics



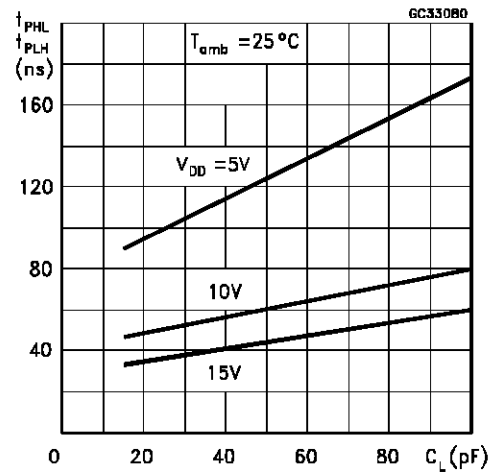
Minimum Output High (source) Current Characteristics



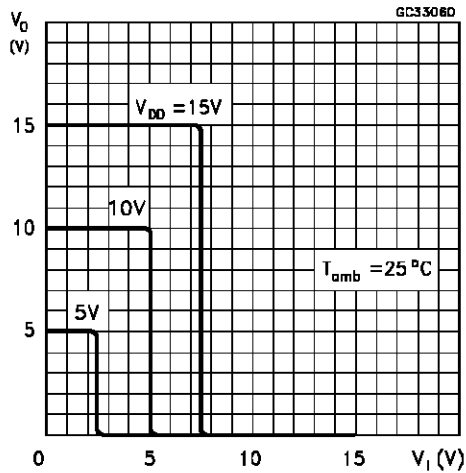
Typical Transition Time vs Load Capacitance



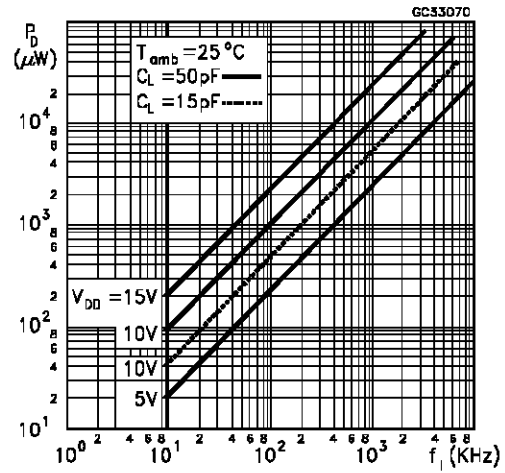
Typical Propagation Delay Time vs Load Capacitance



Typical Voltage Transfer Characteristics as a Function of Temperature

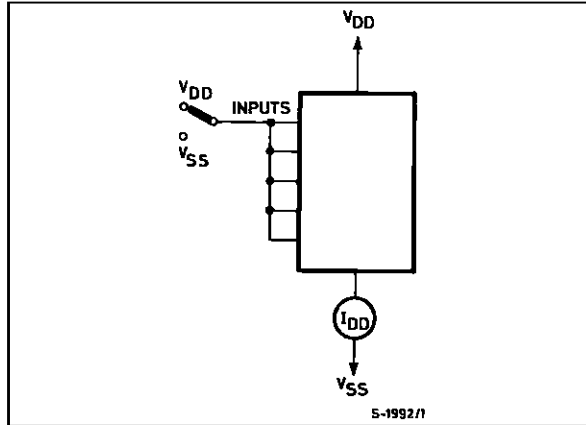


Typical Power Dissipation Per Gate vs Frequency

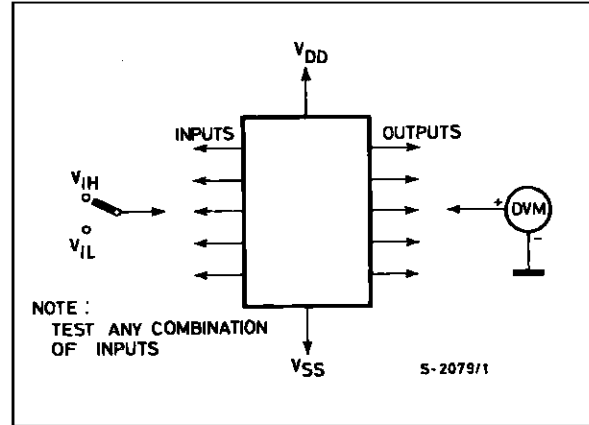


TEST CIRCUITS

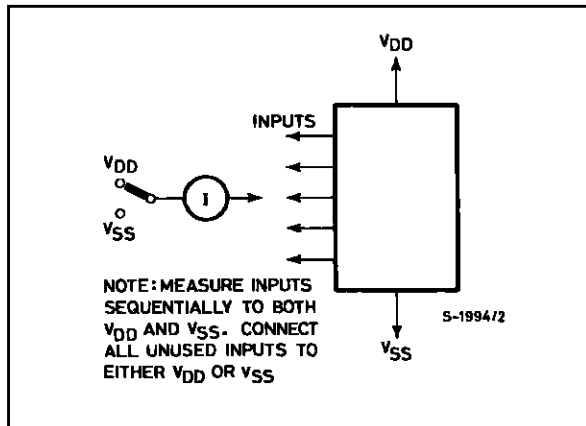
Quiescent Device Current



Noise Immunity.

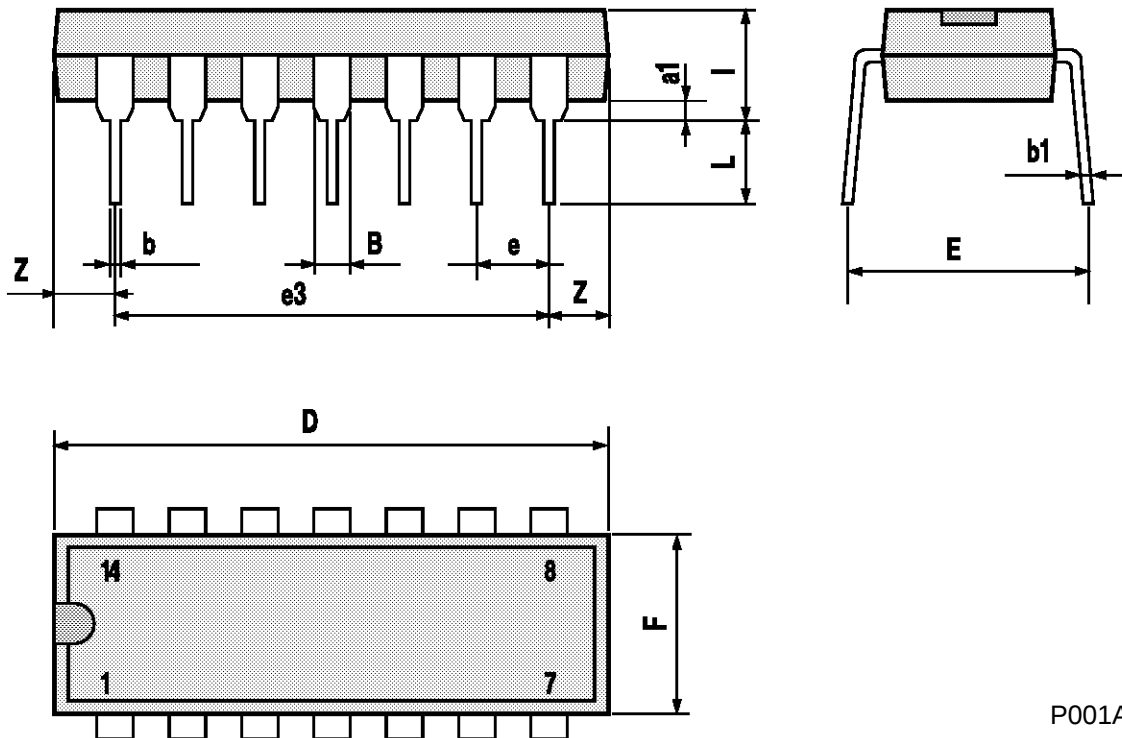


Input Leakage Current.



Plastic DIP14 MECHANICAL DATA

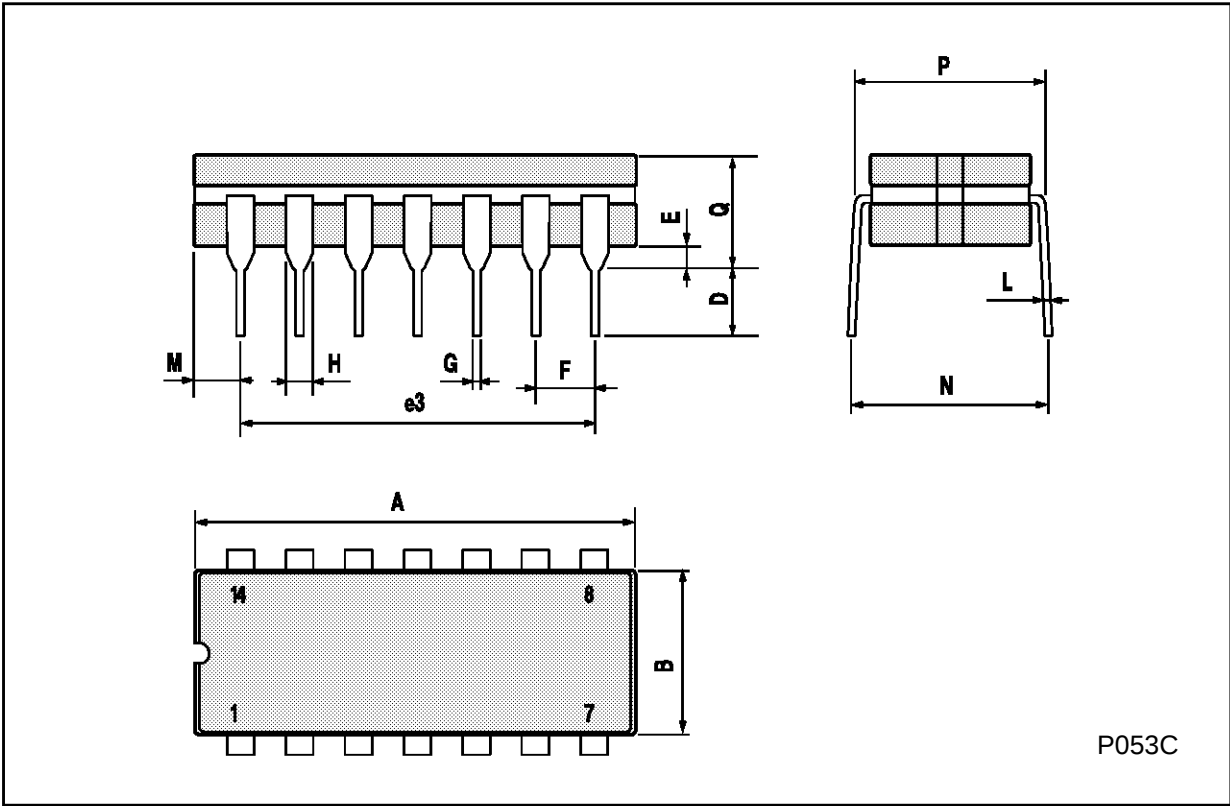
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
B	1.39		1.65	0.055		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
e		2.54			0.100	
e3		15.24			0.600	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z	1.27		2.54	0.050		0.100



P001A

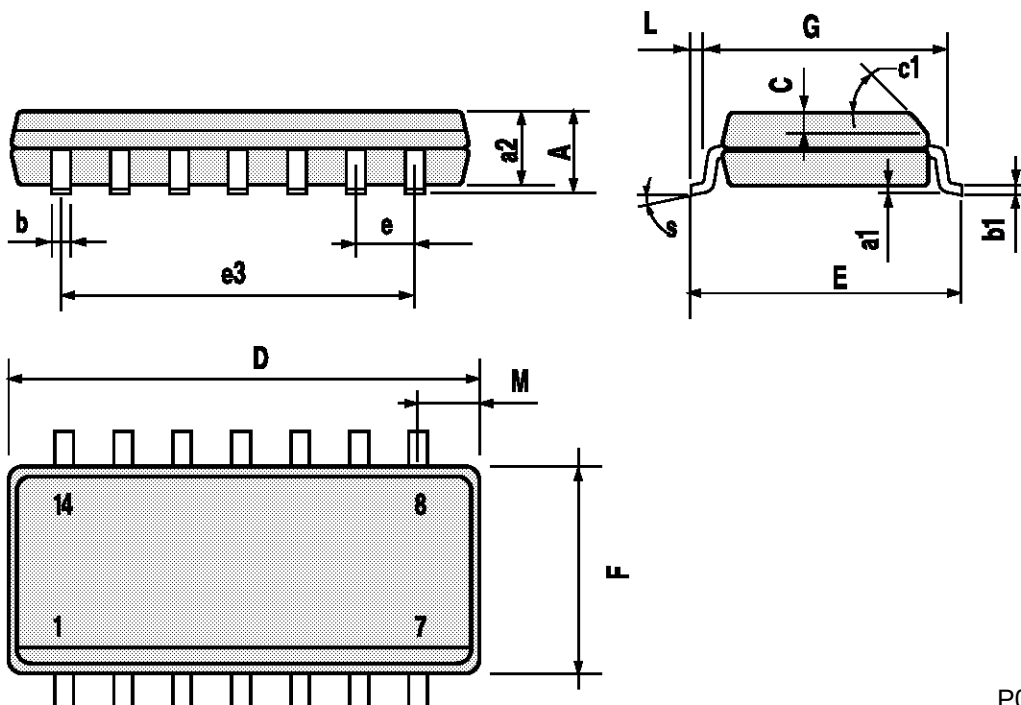
Ceramic DIP14/1 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			20			0.787
B			7.0			0.276
D		3.3			0.130	
E	0.38			0.015		
e3		15.24			0.600	
F	2.29		2.79	0.090		0.110
G	0.4		0.55	0.016		0.022
H	1.17		1.52	0.046		0.060
L	0.22		0.31	0.009		0.012
M	1.52		2.54	0.060		0.100
N			10.3			0.406
P	7.8		8.05	0.307		0.317
Q			5.08			0.200



SO14 MECHANICAL DATA

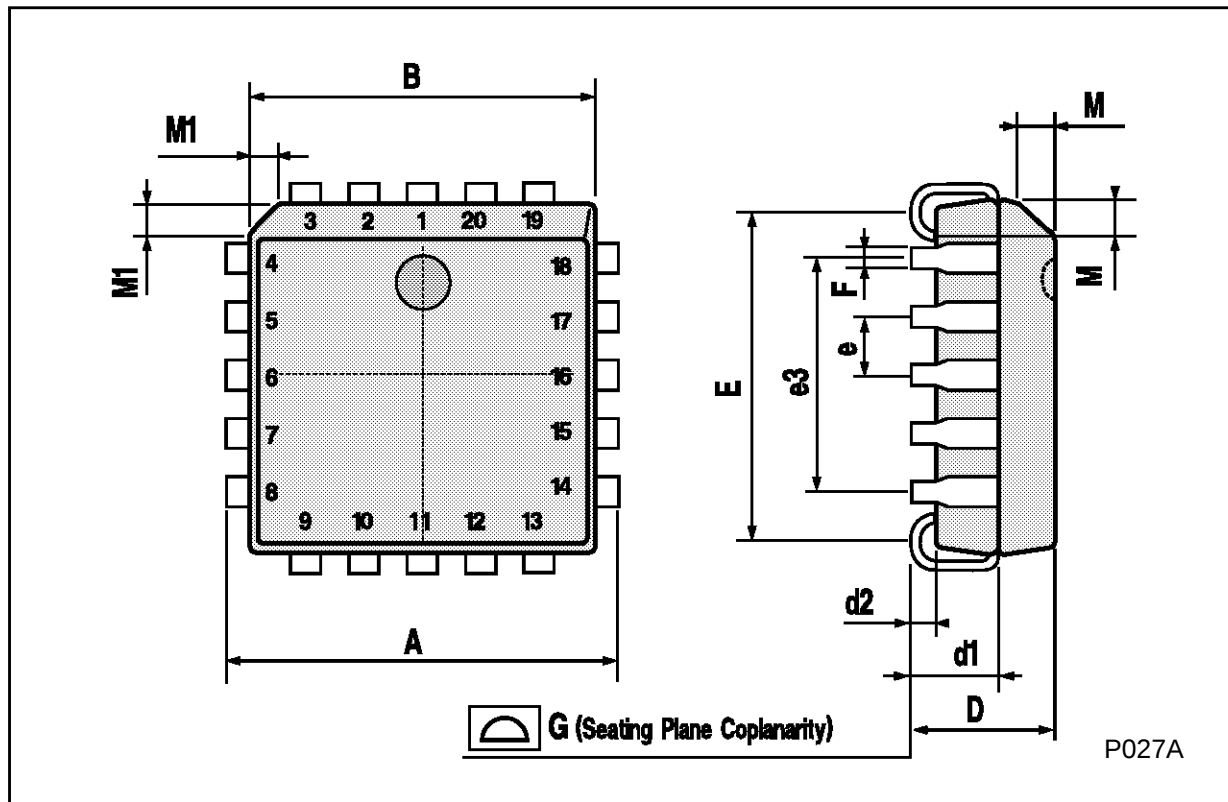
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.2	0.003		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
C		0.5			0.019	
c1	45° (typ.)					
D	8.55		8.75	0.336		0.344
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		7.62			0.300	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
M			0.68			0.026
S	8° (max.)					



P013G

PLCC20 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	9.78		10.03	0.385		0.395
B	8.89		9.04	0.350		0.356
D	4.2		4.57	0.165		0.180
d1		2.54			0.100	
d2		0.56			0.022	
E	7.37		8.38	0.290		0.330
e		1.27			0.050	
e3		5.08			0.200	
F		0.38			0.015	
G			0.101			0.004
M		1.27			0.050	
M1		1.14			0.045	



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